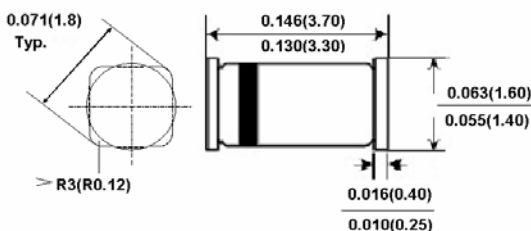
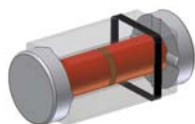


LS4448 /LS4148/LS914B

500mW Hermetically Sealed Glass Fast Switching Diodes

QUADRO MINI MELF



Dimensions in inches and (millimeters)

Features

- ✧ Fast switching device ($T_{RR} < 4.0\text{nS}$)
- ✧ Quadro Mini-MELF package
- ✧ Surface device type mounting
- ✧ Hermetically sealed glass
- ✧ Compression bonded construction
- ✧ All external surfaces are corrosion resistant and leads are readily solderable
- ✧ RoHS compliant
- ✧ Matte Tin (Sn) lead finish
- ✧ 1st band indicates cathode

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Maximum Ratings

Type Number	Symbol	Value	Units
Power Dissipation	P_d	500	mW
Working Inverse Voltage	W_{IV}	75	V
Non-repetitive Peak Forward Current	I_{FM}	450	mA
Average Rectified Current	I_o	150	mA
Peak Forward Surge Current	I_{FSURGE}	2	A
Operating Junction Temperature	T_J	175	°C
Storage Temperature Range	T_{STG}	-65 to + 200	°C

Electrical Characteristics

Type Number	Symbol	Min	Max	Units
Breakdown Voltage IR=100uA IR=5uA	B_V	100 75		V
Forward Voltage LS4448, LS914B IF=5.0mA LS4148 IF= 10mA LS4448, LS914B IF =100mA	V_F	0.62 -	0.72 1.0 1.0	V
Reverse Leakage Current VR=20V VR=75V	I_R		25 5	nA uA
Junction Capacitance VR=0, f=1.0MHz	C_j	-	4.0	pF
Reverse Recovery Time (Note 1)	t_{rr}	-	4.0	nS

Notes: 1. Reverse Recovery Test Conditions: $I_F=I_R=10\text{mA}$, $R_L=100\Omega$, $I_{RR}=1\text{mA}$

RATINGS AND CHARACTERISTIC CURVES (LS4448/LS4148/LS914B)

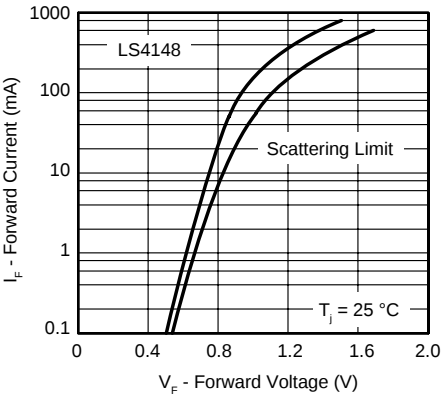


Figure 1. Forward Current vs. Forward Voltage

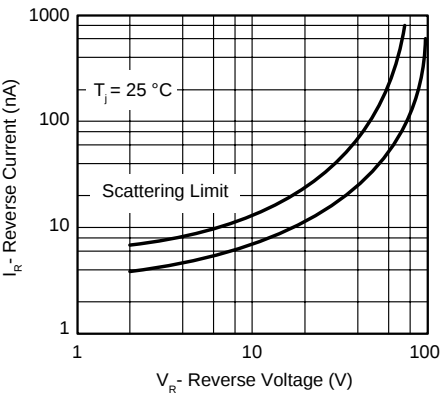


Figure 3. Reverse Current vs. Reverse Voltage

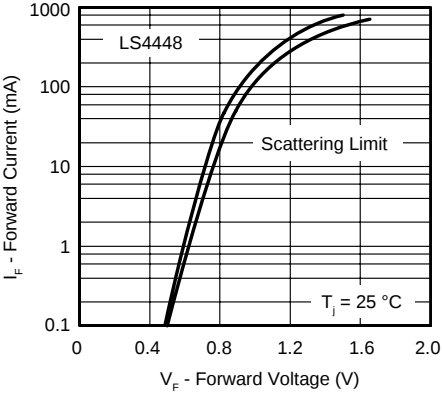


Figure 2. Forward Current vs. Forward Voltage

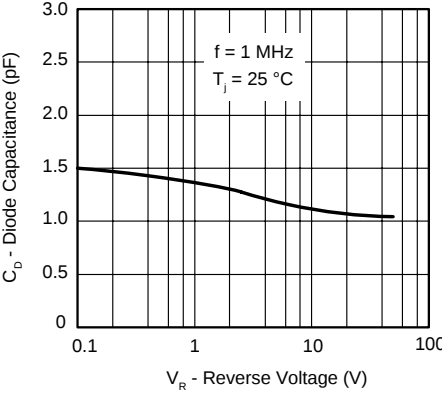


Figure 4. Diode Capacitance vs. Reverse Voltage